

FAN73832 Half-Bridge Gate-Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 350mA/650mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V_S Swing to -9.8V for Signal Propagation at V_{DD}=V_{BS}=15V
- High-Side Output in Phase of IN Signal
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Canceling Circuit
- Internal 400ns Minimum Dead-Time at R_{DT}=20KΩ
- Programmable Turn-on Delay-Time Control (Dead-Time)

Applications

- SMPS
- Motor Drive Inverter
- Fluorescent Lamp Ballast
- HID Ballast

Description

The FAN73832 is a half-bridge, gate-drive IC with shutdown and programmable dead-time control functions for driving MOSFETs and IGBTs, operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side driver under high dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to V_{S} =-9.8V (typical) for V_{BS} =15V.

The UVLO circuits for both channels prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

Output drivers typically source/sink 350mA/650mA, respectively, which is suitable for all kinds of half- and full-bridge inverters.





Ordering Information

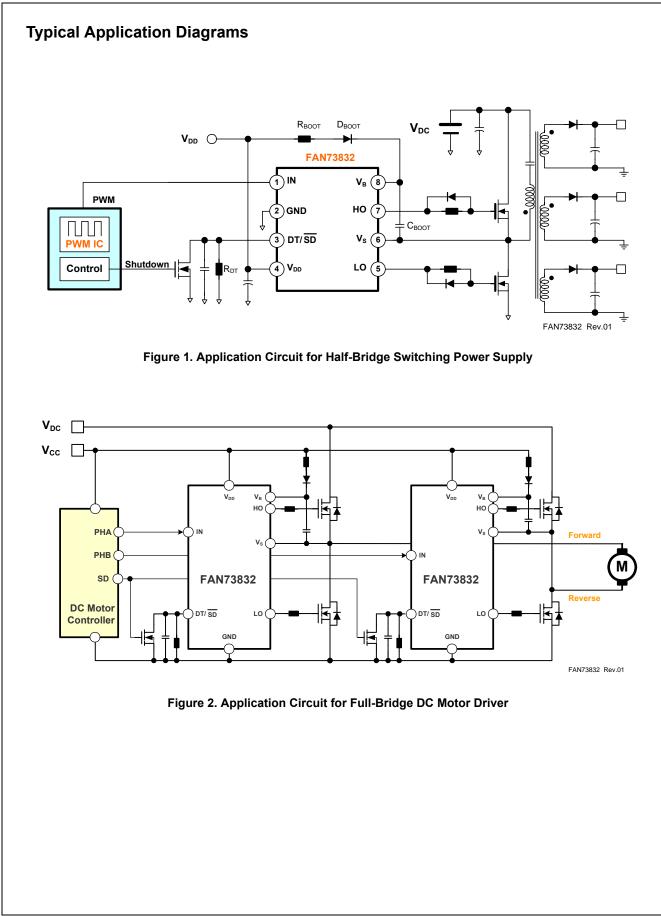
Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN73832M ⁽¹⁾	8-SOP			Tube
FAN73832MX ⁽¹⁾	0-30F	Yes	-40°C ~ 125°C	Tape & Reel
FAN73832N	8-DIP			Tube

Note:

1. These devices passed wave soldering test by JESD22A-111.

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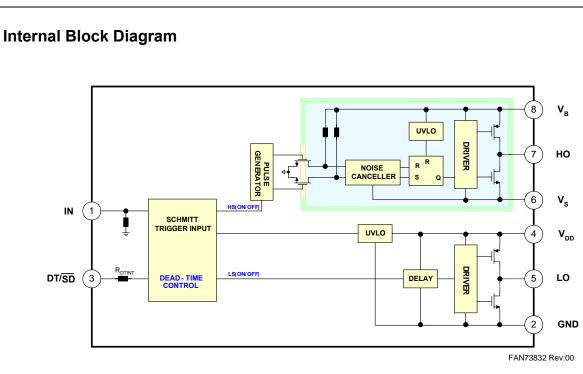


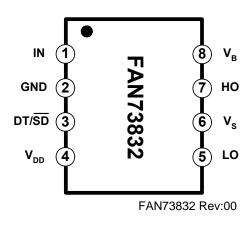
Figure 3. Functional Block Diagram of FAN73832

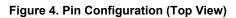
IN

DT/SD

FAN73832 Half-Bridge Gate-Drive IC

Pin Assignments





Pin Definitions

Pin #	Name	Description	
1	IN	Logic Input	
2	GND	Ground	
3	DT/SD	Dead-Time Control with External Resistor and Shutdown Function	
4	V _{DD}	w-Side Supply Voltage	
5	LO	w-Side Driver Output	
6	Vs	gh-Side Floating Supply Return	
7	НО	High-Side Driver Output	
8	V _B	High-Side Floating Supply	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$ unless otherwise specified.

Symbol	Parameter		Min.	Max.	Unit
V _S	High-side offset voltage		V _B -25	V _B +0.3	V
V _B	High-side floating supply voltage		-0.3	625	V
V _{HO}	High-side floating output voltage HO		V _S -0.3	V _B +0.3	V
V _{DD}	Low-side and logic-fixed supply voltage		-0.3	25	V
V _{LO}	Low-side output voltage LO		-0.3	V _{DD} +0.3	V
V _{IN}	Logic input voltage (IN)		-0.3	V _{DD} +0.3	V
V _{DT/SD}	Dead-time and shutdown control voltage		-0.3	5.0	V
GND	Logic ground		V _{DD} -25	V _{DD} +0.3	V
dV _S /dt	Allowable offset voltage slew rate			50	V/ns
Pn ⁽²⁾⁽³⁾⁽⁴⁾	Power dissipation	8-SOP		0.625	W
PD		8-DIP		1.25	
0	Thermal registered, junction to embient	8-SOP		200	°C/W
θ_{JA}	Thermal resistance, junction-to-ambient	8-DIP		100	-0/10
TJ	Junction temperature			150	°C
T _{STG}	Storage temperature			150	°C

Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 3. Refer to the following standards:

JESD51-2: Integral circuits thermal test method environmental conditions - Natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages

4. Do not exceed P_D under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Condition	Min.	Max.	Unit
VB	High-side floating supply voltage		V _S +15	V _S +20	V
V _S	High-side floating supply offset voltage 6-V _{DD} 60		600	V	
V _{DD}	Low-side supply voltage		15	20	V
V _{HO}	High-side (HO) output voltage		Vs	VB	V
V _{LO}	Low-side (LO) output voltage		GND	V _{DD}	V
V _{IN}	Logic input voltage (IN)		GND	V _{DD}	V
T _A	Ambient temperature		-40	125	°C

Electrical Characteristics

 V_{BIAS} (V_{DD} , V_{BS})=15.0V, R_{DT} =20K Ω , T_A =25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are referenced to V_S and COM and are applicable to the respective outputs HO and LO.

Symbol	Parameter Condition		Min.	Тур.	Max.	Unit	
SUPPLY C	URRENT SECTION						
I _{QBS}	Quiescent V _{BS} supply current	V _{IN} =0V or 5V		35	90		
I _{QDD}	Quiescent V _{DD} supply current	V_{IN} =0V or 5V, R _{DT} =20K Ω		300	450		
I _{SD} ⁽⁵⁾	Shutdown supply current	DT/SD=GND		650	900		
I _{PBS}	Operating V _{BS} supply current	f _{IN} =20kHz, rms value		400	700	μA	
I _{PDD}	Operating V _{DD} supply current	f _{IN} =20kHz, rms value		650	850		
I _{LK}	Offset supply leakage current	V _B =V _S =600V			10		
POWER SI	JPPLY SECTION						
V _{DDUV+} V _{BSUV+}	V _{DD} and V _{BS} supply under-voltage positive going threshold		10.7	11.6	12.5	V	
V _{DDUV-} V _{BSUV-}	V _{DD} and V _{BS} supply under-voltage negative going threshold		10.0	10.8	11.6	V	
V _{DDUVH} V _{BSUVH}	V _{DD} supply under-voltage lockout hysteresis			0.8		V	
DEAD-TIM	E CONTROL SECTION						
R _{DTINT}	Internal dead-time setting resistance			20		KΩ	
V _{DT}	Normal voltage at DT	R _{DT} =20KΩ		3.0		V	
GATE DRI	/ER OUTPUT SECTION			•			
V _{OH}	High-level output voltage, V _{BIAS} -V _O	I _O =20mA			1.0	V	
V _{OL}	Low-level output voltage, V _O				0.6	V	
I _{O+}	Output high short-circuit pulse current	$V_{O}\!\!=\!\!0V\!,V_{IN}\!\!=\!\!5V$ with PW<10 $\!\mu s$	250	350		mA	
I _{O-}	Output low short-circuit pulsed current	$V_{O}\text{=}15V,$ $V_{IN}\text{=}0V$ with PW<10 μs	500	650		mA	
V _S	V _S Allowable negative V _S pin voltage for IN signal propagation to HO			-9.8	-7.0	V	
LOGIC INP	UT SECTION (INPUT and SHUTDOWN)			•			
V _{IH}	Logic "1" input voltage		2.9			V	
V _{IL}	Logic "0" input voltage				1.2	V	
I _{IN+}	Logic "1" input bias current	V _{IN} =5V		50	100	μA	
I _{IN-}	Logic "0" input bias current	V _{IN} =0V			2.0	μA	
SD+	Shutdown "1" input voltage				1.2	V	
SD-	Shutdown "0" input voltage		2.9			V	
R _{PD}	Input pull-down resistance			100		KΩ	

Note:

5. This parameter guaranteed by design.

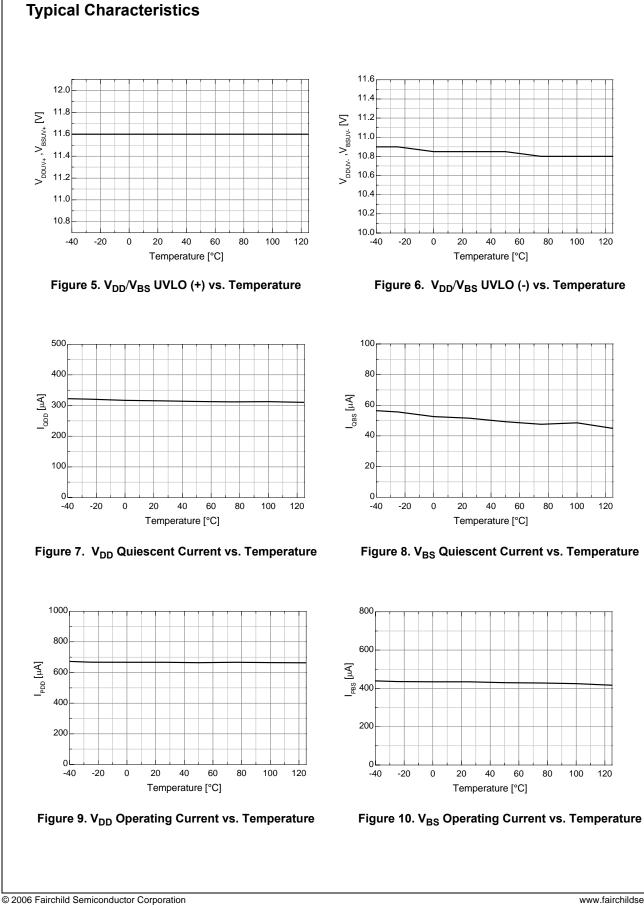
Dynamic Electrical Characteristics

 $V_{BIAS} (V_{DD}, V_{BS}) = 15.0V, V_{S} = GND, C_{L} = 1000 pF, R_{DT} = 20 K\Omega \text{ and } T_{A} = 25^{\circ}C, \text{ unless otherwise specified.}$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
t _{ON}	Turn-on propagation delay	V_{S} =0V, R_{DT} =20K Ω		580	730		
t _{OFF}	Turn-off propagation delay	V_{S} =0V or 600V ⁽⁵⁾ , R _{DT} =20K Ω		180	230		
t _R	Turn-on rise time	C _L =1000pF		50	100	ns	
t _F	Turn-off fall time	C _L =1000pF		30	80		
t _{SD} ⁽⁵⁾	Shutdown propagation delay			100	180		
DT1, DT2	Dead-time LO OFF to HO ON & HO	R _{DT} =20KΩ	300	400	500	ns	
011, 012	OFF to LO ON	R _{DT} = 200KΩ	1.20	1.68	2.30	μs	
DMT	Deed time metabing	R _{DT} = 20KΩ		0	60	200	
וויוש	Dead-time matching	R _{DT} =200KΩ		0	150	ns	

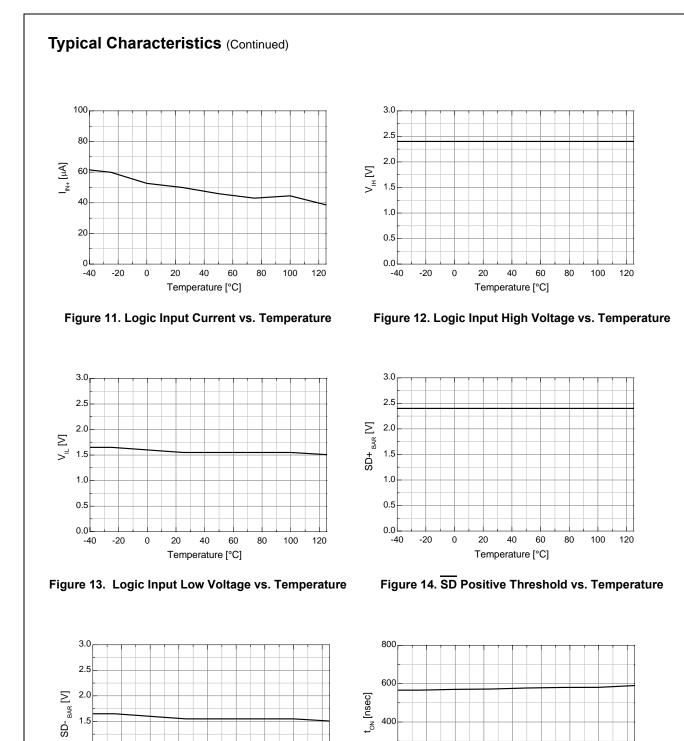
Note:

5. These parameters guaranteed by design.



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1.0

0.5 0.0

-40

-20

0

20

40

Temperature [°C]

Figure 15. SD Negative Threshold vs. Temperature

60

80

100

120

200

0

-40

-20

0

20

40

Temperature [°C]

Figure 16. Turn-on Delay Time vs. Temperature

60

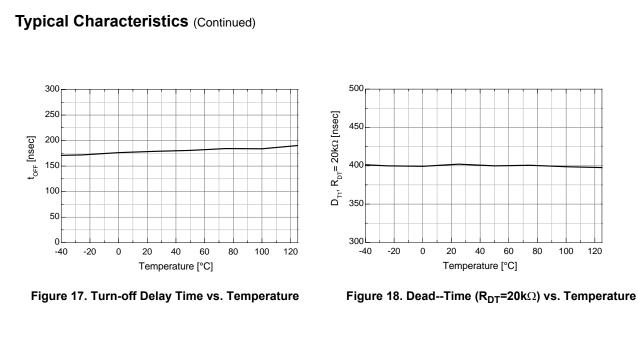
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80

100

120

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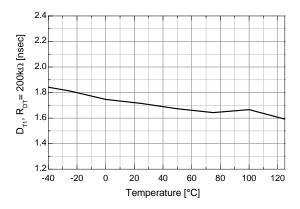
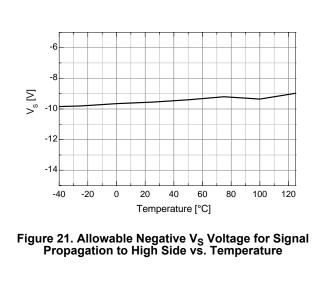


Figure 19. Dead Time (R_{DT}=200k Ω) vs. Temperature



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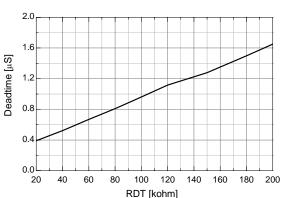
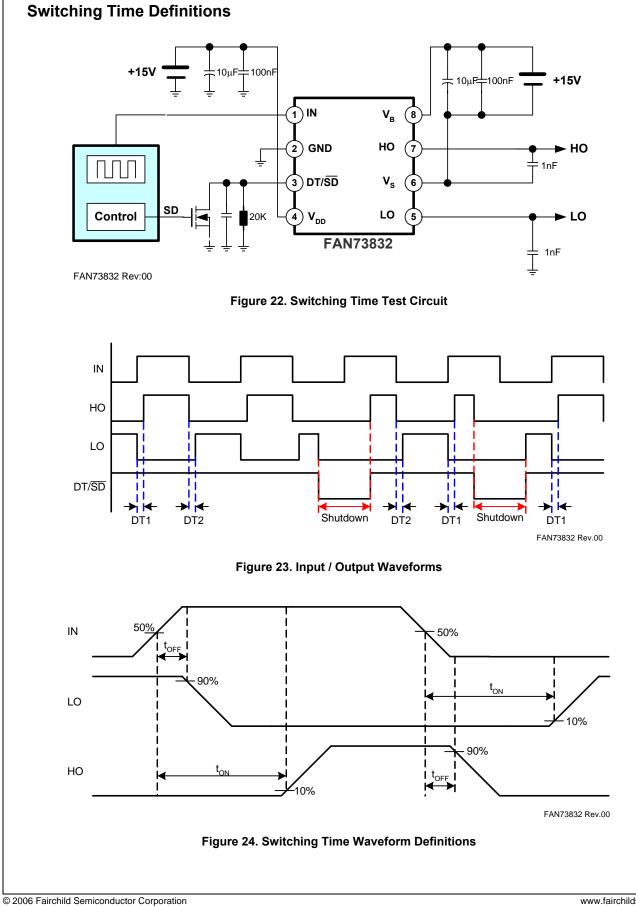


Figure 20. R_{DT} vs. Dead-Time





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50% DT/SD 90% HO or LO ۱_{SD} FAN73832 Rev.00 Figure 25. Shutdown Waveform Definition 90% HO 10% DT2 DT1 90% LO MDT= DT1 - DT2 10% FAN73832 Rev.00 Figure 26. Dead-Time Control Waveform Definition

FAN73832 Half-Bridge Gate-Drive IC

Typical Application Information

1. Normal Operating Consideration

The FAN73832 is a single PWM input, half-bridge, gatedrive IC with programmable dead-time and shutdown functions.

The dead-time is set with a resistor (R_{DT}) at the DT/SD pin. The wide dead-time programming range provides the flexibility to optimize drive signal timing for a selection of switching devices (MOSFET or IGBT) and applications.

The turn-on time delay circuitry (Dead-Time) accommodates resistor values from $20k\Omega$ to $200k\Omega$ with a dead-time proportional to the R_{DT} resistance.

If the DT/SD pin voltage decreases below 1.2V in the normal operation, the IC enters shutdown mode.

The external dead-time setting resistor (R_{DT}) is at least above 20K Ω for normal operation in typical applications.

2. Under-Voltage Lockout (UVLO)

The FAN73832 has an under-voltage lockout (UVLO) protection circuit for high- and low-side channels to prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage. The UVLO circuitry monitors the supply voltage (V_{DD}) and bootstrap capacitor voltage (V_{BS}) antepenult.

3. Layout Consideration

For optimum performance of the high- and low-side gate drivers, considerations must be taken during printed circuit board (PCB) layout.

3.1 Supply Capacitors

If the output stages are able to quickly turn-on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins (V_{DD} and GND for the ground-tied supply, V_B and V_S for the floating supply) to minimize parasitic inductance and resistance.

3.2 Gate Drive Loop

Current loops behave like an antenna, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performances, gate drive loops must be reduced as much as possible.

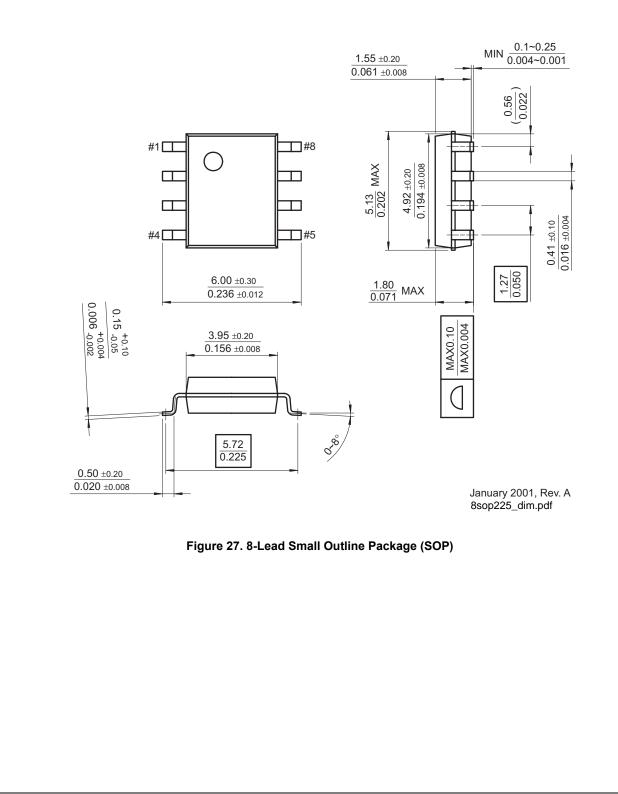
3.3 Ground Plane

Ground plane must not be placed under or nearby the high-voltage floating side to minimize noise coupling.

Mechanical Dimensions

8-SOP

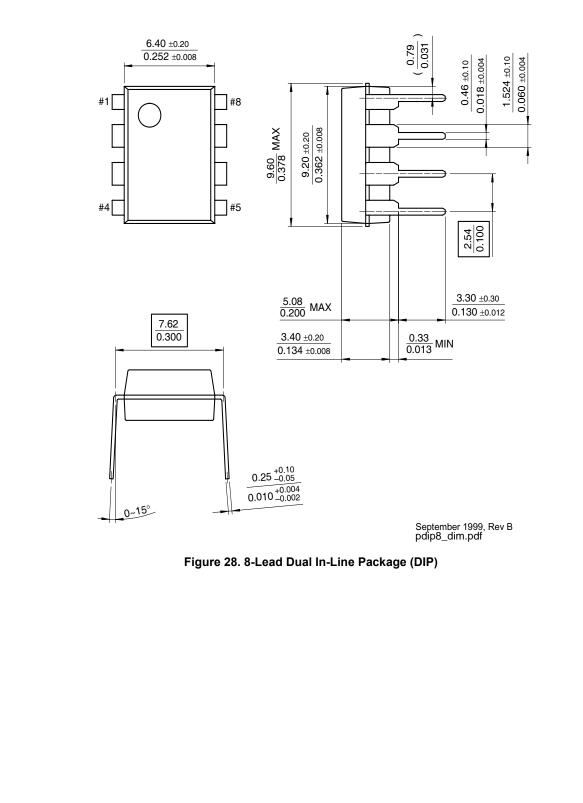
Dimensions are in millimeters (inches) unless otherwise noted.



Mechanical Dimensions (Continued)

8-DIP

Dimensions are in millimeters (inches) unless otherwise noted.



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